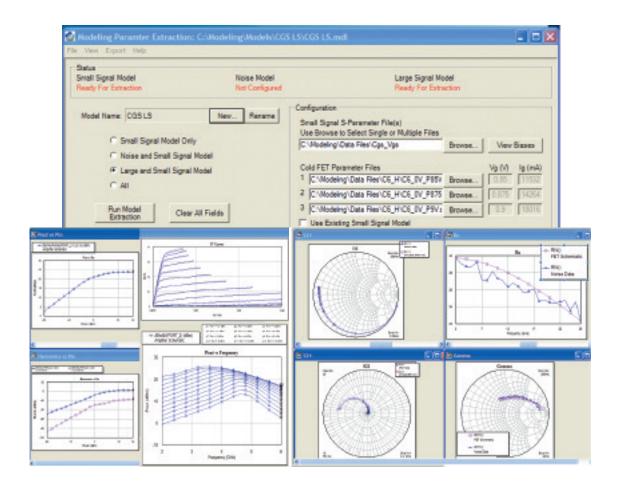
Device Modeling and Characterization Services

Auriga can be your cost- and time-efficient modeling and characterization lab...

Auriga can be your company's high-frequency, high-power RF microwave expert.



Precise. Dependable. Timely.





Device Modeling and **Characterization** Services

Unparalleled modeling and characterizations services

Auriga's Device Modeling and Characterization Services Group is a great addition to your R&D, design, or production test team.

Successful device modeling requires both an accurate model and accurate measurements. Auriga has the expertise of both disciplines – helping you achieve "first-pass" design success.

Successful extraction of models resulted in scaling a large power device from 50W up to 150W.

The Auriga Services Group leverages more than 75-years experience of modeling and characterizing high-frequency, high-power RF microwave devices. The Group is built around Dr. Yusuke Tajima, co-creator of the Tajima-Hsu Model. Dr. Tajima's philosophy of becoming an "extension of your team" is present in every project Auriga undertakes.

Whether you need; consulting services for a new design, a model created on a current device, characterization of your product's performance, validation of your test results, or supplemental support for an overburdened team, Auriga can help.

Auriga's state-of-the-art lab, based in Massachusetts, is fully functional and ready to use 24/7.

Standard Auriga lab systems available (partial list)

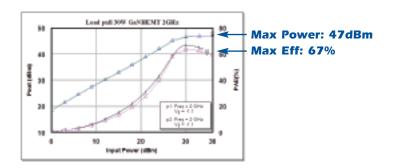
- DC IV or pulsed IV
- CW or pulsed RF
- Large signal harmonic Load Pull
- Noise parameter

Standard device models (partial list)

- MESFET and PHEMT: Tajima-Hsu, Materka, Angelov2
- LDMOS: MOS11
- BJT and HBT: Gummel-Poon, VBIC, Root

Wide-range of services (partial list)

- Wafer level, chips, or fixtured devices
- Pulsed IV down to 200ns
- S-parameters 10MHz to 50GHz
- Load Pull 800MHz to 50GHz
- Noise parameters 300MHz to 50GHz



Example of simulated results using Auriga Model compared to the measured data of a 50W GaN HEMT device

